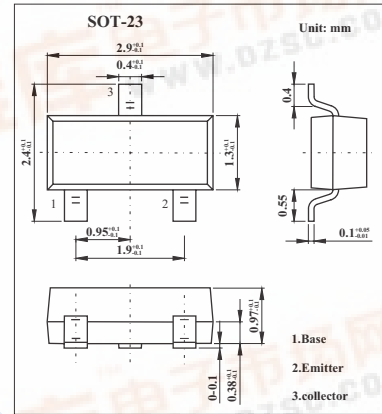


SMD Type Transistors

NPN Medium Frequency Transistor
KFS20(BFS20)

Features

- Low current (max. 25 mA)
- Low voltage (max. 20 V)
- Very low feedback capacitance (typ. 350 fF).



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	VCBO	30	V
Collector-emitter voltage	VCEO	20	V
Emitter-base voltage	VEBO	4	V
Collector current	IC	25	mA
Peak collector current	ICM	25	mA
power dissipation	PD	250	mW
Thermal resistance from junction to ambient *	Rth j-a	500	K/W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-65 to +150	°C

* Transistor mounted on an FR4 printed-circuit board.

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	IE = 0; VCB = 20 V			100	nA
	ICBO	IE = 0; VCB = 20 V; Tj = 100 °C			10	μA
Emitter cutoff current	IEBO	IC = 0; VEB = 4V			100	nA
DC current gain	hFE	IC = 7mA; VCE = 10 V	40	85		
Base to emitter voltage	VBE	IC = 7 mA; VCE = 10V		740	900	mV
Collector capacitance	CC	IE = ie = 0; VCB = 10 V; f = 1 MHz		1		pF
Freedback capacitance	Cre	IC=0,VCB=10V,f=1MHz		350		pF
Transition frequency	fT	IC =5mA; VCE =10 V; f = 100 MHz	275	450		MHz

Marking

Marking	G1
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